



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:  
Shubneesh Batra et al.

Serial No.: 09/901,837

Filed: July 10, 2001

For: LOW TEMPERATURE REFLOW  
METHOD FOR FILLING HIGH  
ASPECT RATIO CONTACTS

Assistant Commissioner  
for Patents  
Washington, D.C. 20231

Sir:

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Group Art Unit: 2825

Examiner: Everhart, C.

Atty Docket: MCRO:199--3/FLE  
95-0057.03

CERTIFICATE OF MAILING  
37 C.F.R. 1.8

I hereby certify that this correspondence is being deposited with the U.S. Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on the date below:

March 7, 2003

Date

Helen Tinsley

AMENDMENT PURSUANT TO 37 CFR 1.116

Please amend the above-identified application, as follows:

IN THE CLAIMS

Please amend claim 1, as follows:

1' (Once Amended). A method of processing a semiconductor substrate, comprising the steps of:

- (a) providing a semiconductor substrate having a surface with a contact formed therein;
- (b) depositing a conductor layer on the semiconductor substrate surface, wherein said conductor layer comprises a conductor;

AF/2825  
#9/  
Gundt C  
(NE)  
A Ford  
3/19/03